Electronic Supplementary Material (ESI) for Nanoscale.

Supporting Information

Difference in hot carrier cooling rate between Langmuir-Blodgett and drop cast PbS QDs films due to strong electron-phonon coupling

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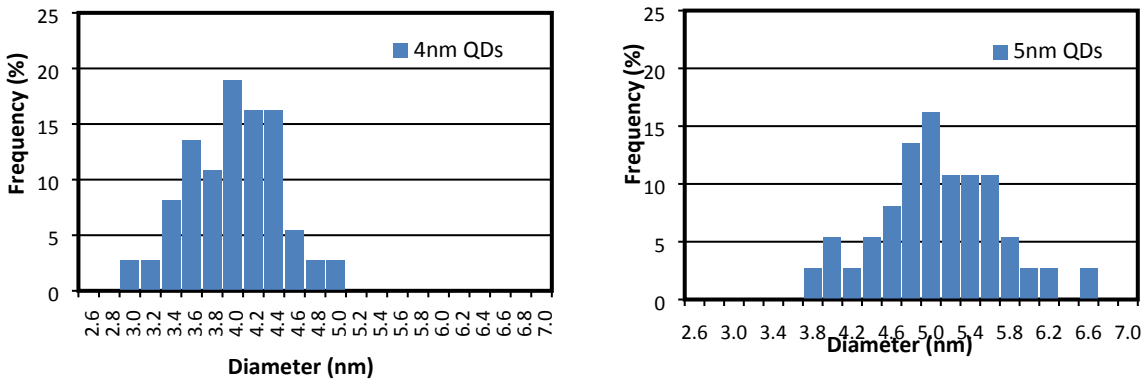

Figure S1. Size distribution histogram plots of 4 nm and 5 nm PbS QDs estimated from TEM images.

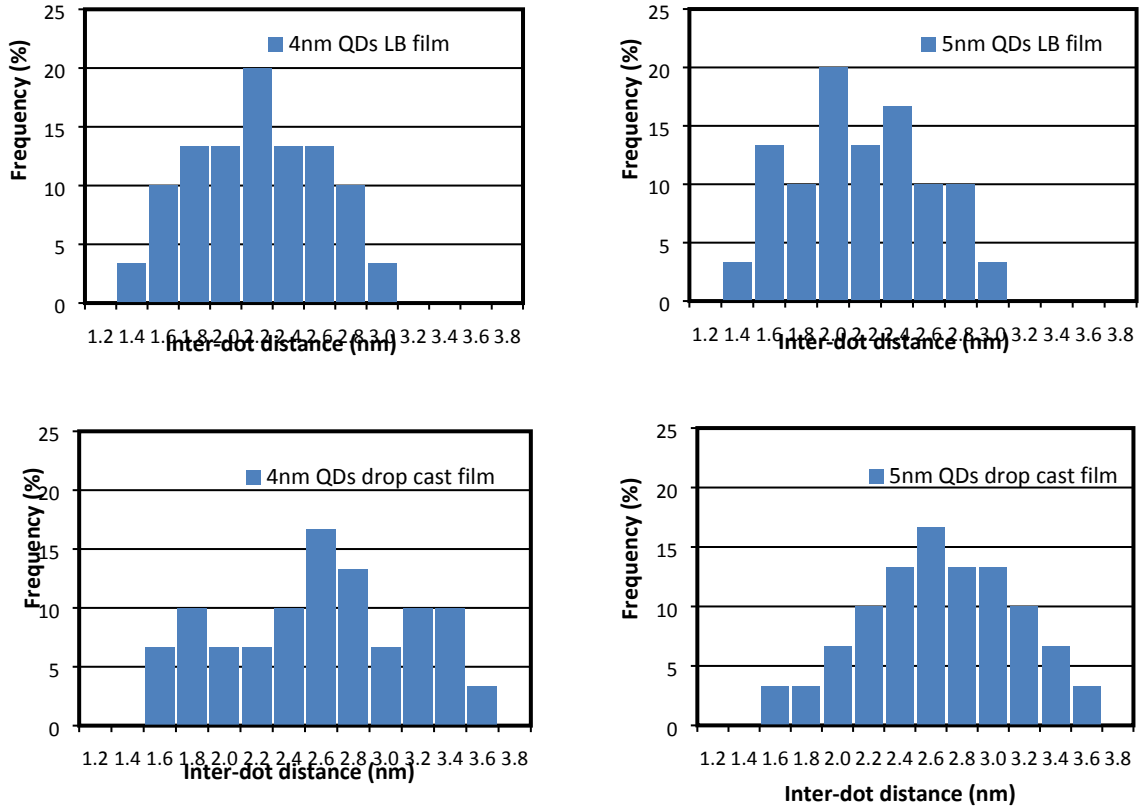

Figure S2. Distribution histograms of the inter-dot distance in the QD LB films and drop cast films.